

PSMN011-60MS

N-channel 60 V 11.3 mΩ standard level MOSFET in LFPAK33
4 June 2013

Product data sheet

1. General description

Standard level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources
- LFPAK33 package is footprint compatible with other 3.3mm types
- Qualified to 175 °C

3. Applications

- AC-to-DC converters
- Synchronous rectification
- DC-DC converters

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	-	61	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	91	W
T _j	junction temperature			-55	-	175	°C
Static charac	teristics				'		
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 12		-	9.6	11.3	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 15 A; V_{DS} = 30 V; T_j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	5.8	-	nC



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simpl	ified outline	Graphic symbol
1	S	source	ĺ		D I
2	S	source			
3	S	source			G C
4	G	gate			mbb076 S
mb	D	mounting base; connected to drain	LF	FPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN011-60MS	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210		

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN011-60MS	M11S60

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C	-	60	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	61	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	43	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4	-	244	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	91	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	70	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	244	Α
Avalanche rug	gedness				'	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 61 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω ; unclamped; Fig. 3		-	48.1	mJ

[1] Continuous current is limited by package

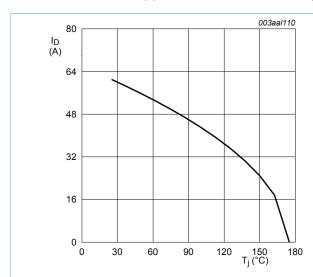


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10 V$

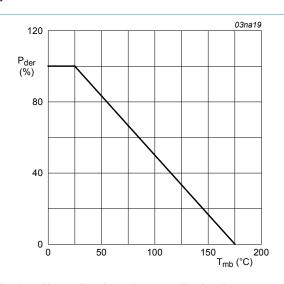


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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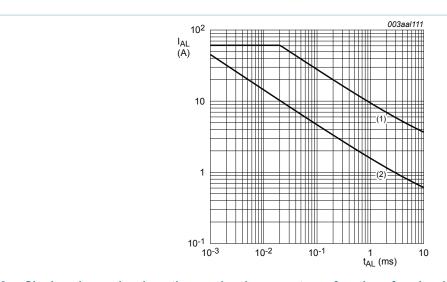
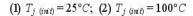


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



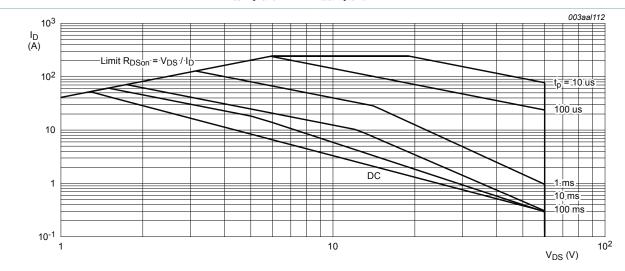


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

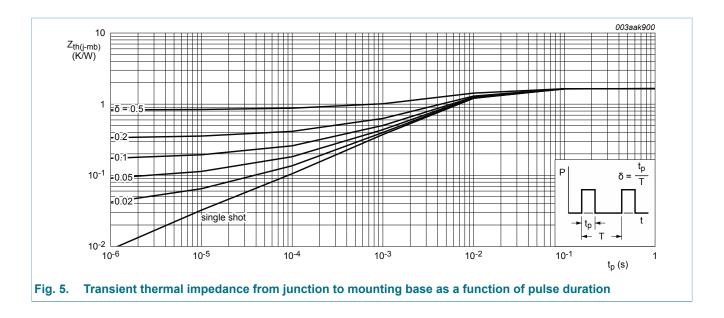
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	1.44	1.65	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS} drain-source		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2.3	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	4.6	V
I _{DSS} C	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.054	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 12	-	9.6	11.3	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; Fig. 13	-	-	24.4	mΩ
R_G	gate resistance	f = 1 MHz	-	2.75	-	Ω
Dynamic ch	naracteristics		1	1		
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 30 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	23	-	nC
		I .				

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q_{GS}	gate-source charge	I _D = 15 A; V _{DS} = 30 V; V _{GS} = 10 V;	-	6.1	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	3.9	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	2.2	-	nC
Q_{GD}	gate-drain charge		-	5.8	-	nC
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$	-	1368	-	pF
C _{oss}	output capacitance		-	191	-	pF
C _{rss}	reverse transfer capacitance		-	108	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 2 Ω; V _{GS} = 10 V;	-	6.7	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	8.46	-	ns
t _{d(off)}	turn-off delay time		-	16.9	-	ns
t _f	fall time		-	9.18	-	ns
Source-drai	in diode		'			
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 17$	-	0.84	1.2	V
t _{rr}	reverse recovery time	$I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	21.7	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	19.2	-	nC

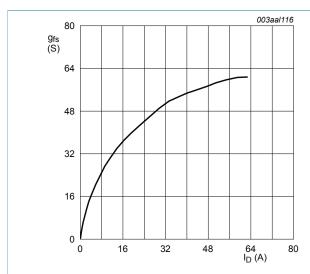


Fig. 6. Forward transconductance as a function of drain current; typical values

$$T_j = 25$$
°C; $V_{DS} = 10V$

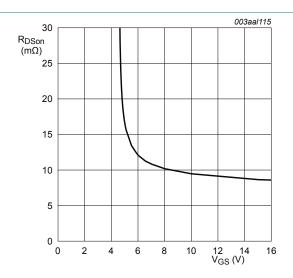


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 15A$

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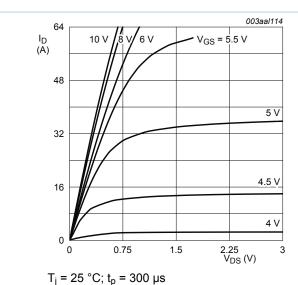


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

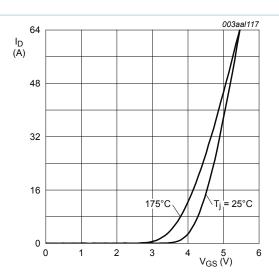


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

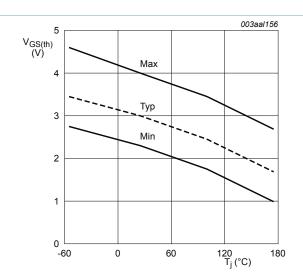


Fig. 10. Gate-source threshold voltage as a function of junction temperature

 $I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$

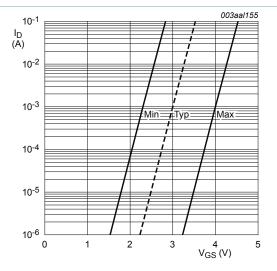


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25$ °C; $V_{DS} = 5V$

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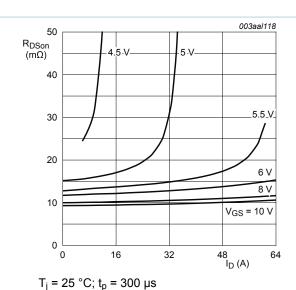


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

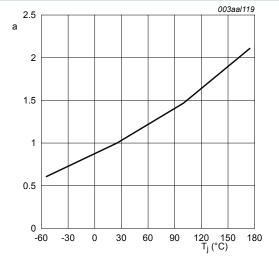


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

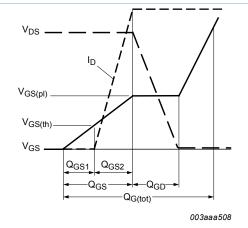


Fig. 14. Gate charge waveform definitions

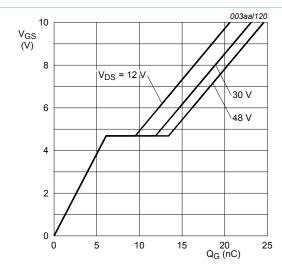


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 15A$

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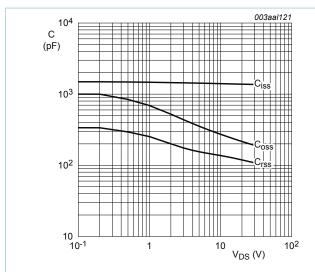
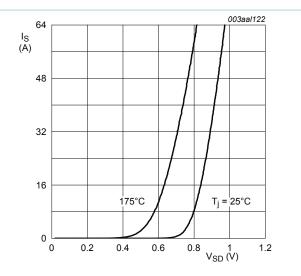


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values

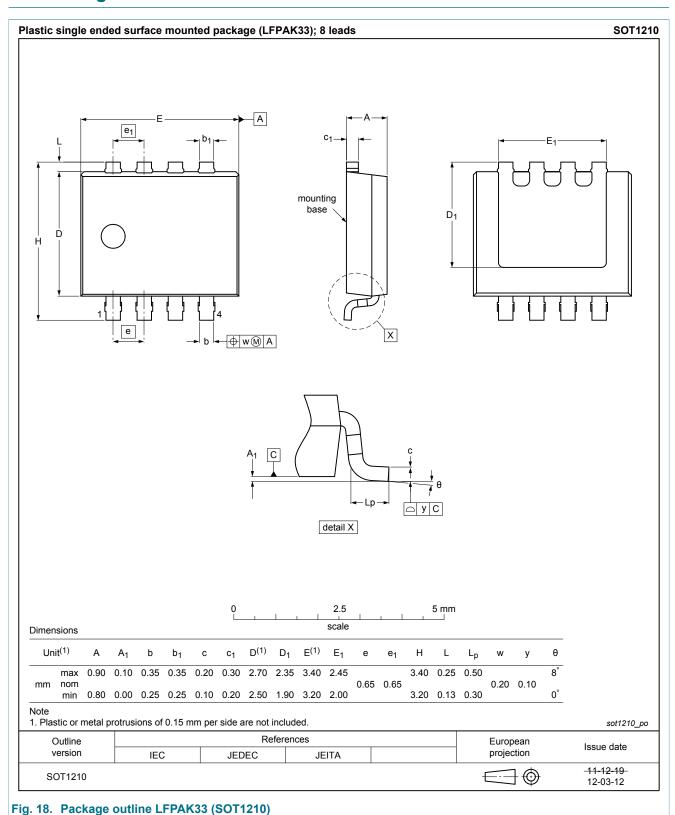
$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$



voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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